L Number	Hits	Search Text	DB	Time stamp
-	720	LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	51	lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	60	lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	479	LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	74	(lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	178	lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	249	lateral$4 near7 (metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	2322	lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	10	LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	5	LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	455	lateral$4 near7 (DMOS or DMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	8141	lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:58

	9373	(LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:02
-	152308	(gate$1 or electrode$1) and source$1 and drain$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:35
-	140917	(field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
-	1922	((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((gate$1 or electrode$1) and source$1 and drain$1) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 17:36

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–	15865	(amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:04
–	39181	(amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:05
–	30917	(amorphous or amorph$9) near3 film$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:11
–	67049	((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:11
–	204	(((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((gate$1 or electrode$1) and source$1 and drain$1) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5))) and (((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:12
–	5147	implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:07

-	69	((((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((gate$1 or electrode$1) and source$1 and drain$1) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5))) and (((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1))) and (implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:25
-	498	(((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) same (implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:47

–		30	((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) same (implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:26
–		330	(((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) with (implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:47

-	22	((((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) with (implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:50
-	23681	(((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:51
-	244	(implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) same ((((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) with (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:51

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–	16	((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) same ((((amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)) or ((amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)) or ((amorphous or amorph$9) near3 film$1)) with (substrate or wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:52
–	720	LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
–	51	lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
–	60	lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
–	479	LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
–	74	(lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
–	178	lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
–	250	lateral$4 near7 (metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57

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-	2322	lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	10	LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	5	LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	455	lateral$4 near7 (DMOS or DMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:58
-	8142	lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:59
-	9374	(LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:03
-	43547	(amorphous or amorph$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:44

−	334	((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide·adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:06
−	5148	implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:13
−	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:09
−	25985	implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:22
−	7645	implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:24
−	26134	(implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25

–	176	((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and (((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25
–	152356	(gate$1 or electrode$1) and source$1 and drain$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
–	141012	(field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:37

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| | | 120 | ((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and (((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer)))) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 18:38 |

| | | 109 | ((gate$1 or electrode$1) and source$1 and drain$1) and ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and (((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer)))) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 18:38 |

–	1255	((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:44
–	280	(((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))) and (amorphous or amorph$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:45

| - | 172 | ((gate$1 or electrode$1) and source$1 and drain$1) and ((field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)) and ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))))) and (amorphous or amorph$9)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 18:46 |

| | | 280 | (((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and (((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer)))) or ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and (amorphous or amorph$9)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 19:54 |

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–	848	((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) with (amorphous or amorph$9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
–	45	(((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) with (amorphous or amorph$9) with (substrate or wafer)) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
–	1853	((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) same (amorphous or amorph$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:58

-	78	(((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) same (amorphous or amorph$9) same (substrate or wafer)) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:58
-	43237	(crystall$9 or re-crystall$9 or (re adj crystall$9)) with amorph$9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:53
-	8629	gaussian with (distribut$6 or profil$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:55

| | | 3 | (((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) with (amorphous or amorph$9) with (substrate or wafer)) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))))) and ((crystall$9 or re-crystall$9 or (re adj crystall$9)) with amorph$9) and (gaussian with (distribut$6 or profil$4)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 21:56 |

| - | | 3 | ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) same (amorphous or amorph$9) same (substrate or wafer)) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))) and ((crystall$9 or re-crystall$9 or (re adj crystall$9)) with amorph$9) and (gaussian with (distribut$6 or profil$4)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 21:56 |

| | | 6 | ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and (((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1)))) and ((amorphous or amorph$9) same (substrate or wafer)))) or ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))) and (amorphous or amorph$9))) and ((crystall$9 or re-crystall$9 or (re adj crystall$9)) with amorph$9) and (gaussian with (distribut$6 or profil$4)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 21:58 |

Search History   10/30/02 11:25:11 AM   Page 20

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| | | 25 | ((((implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion$1 or atom$1)))) with (amorphous or amorph$9) with (substrate or wafer)) and ((LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)) or (lateral$4 near7 (DMOS or DMOSFET$1)) or (lateral$4 adj8 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1 or FET$1 or transistor$1 or IGFET$1 or (insulat$5 adj gate adj field adj effect adj transistor$1))))) and ((crystall$9 or re-crystall$9 or (re adj crystall$9)) with amorph$9) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 21:59 |

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| - | | 35 | (((((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) same (amorphous or amorph\$9) same (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/18 21:59 |
| - | | 1 | ("5874768").PN. | USPAT; US-PGPUB | 2002/03/19 16:21 |

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Errors
1	BRS	L1	876	LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:20			0
2	BRS	L2	93	lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:32			0
3	BRS	L3	79	lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1 or NMOS or PMOS or NMOSFET$1 or PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:22			0
4	BRS	L4	277	(lateral$4 adj double adj diffus$5 adj ((metal adj oxide adj semiconduct$4) or MOS$2 or MOSFET$1 or PMOS$2 or PMOSFET$1 or NMOS$2 or NMOSFET$1)) or (lateral$4 adj double-diffus$5 adj ((metal adj oxide adj semiconduct$4) or MOS$2 or MOSFET$1 or PMOS$2 or PMOSFET$1 or NMOS$2 or NMOSFET$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:27			0
5	BRS	L7	104	lateral$4 adj diffus$5 adj3 metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:32			0

Type		L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
6	BRS	L5	9	LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:33			0
7	BRS	L6	5	LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
8	BRS	L8	982	1 or 2 or 3 or 4 or 5 or 6 or 7.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
9	BRS	L9	160596	(gate$1 or electrode$1) and source$1 and drain$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:38			0
10	BRS	L10	16999	(amorphous or amorph$9) near3 (region$1 or area$1 or part$1 or portion$1 or element$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
11	BRS	L11	41155	(amorphous or amorph$9) near3 (layer$1 or substrate$1 or wafer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
12	BRS	L12	10445	(amorphous or amorph$9) near3 surfac$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13 BRS	L13	5506	implant$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:25			0
14 BRS	L14	9	8 and 9 and (10 or 11 or 12) and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:44			0
15 BRS	L15	32605	implant$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:44			0
16 BRS	L16	54828	10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:26			0
17 BRS	L17	2443	15 same 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:26			0
18 BRS	L18	9	8 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:35			0
19 BRS	L19	114	8 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:35			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error ors
20 BRS	L20	2855	(implant$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)) with (amorphous or amorph$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:44			0
21 BRS	L21	3000	implant$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium) with (amorphous or amorph$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:50			0
22 BRS	L22	8	8 and 21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:46			0
23 BRS	L23	3809	(implant$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium) same (amorphous or amorph$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:51			0
24 BRS	L24	10	8 and 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:51			0

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25 BRS	L25	9546	(LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 near7 (MOS or MOSFET$1 or NMOS or PMOS or NMOSFET$1 or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:56			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Errors
27	BRS	L27	25	25 or 26	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:59			0
26	BRS	L26	9546	(LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)) or (lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj diffus$5 adj MOSFET$1)) or (lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)) or (LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)) or ((lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4) or (lateral$4 near7 (MOS or double-diffus$5 adj metal adj oxide adj semiconduct$4)) or (lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)) or (lateral$4 near7 (metal adj oxide adj semiconduct$4)) or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)) or (LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)) or (LDNMOS$2 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:58			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L28	9546	8 or 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:59			0
29	BRS	L29	123	21 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 15:01			0
30	BRS	L30	149	23 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 15:01			0

10/20/2002, EAST Version: 1.03.0002

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31	IS&R	L31	38	(("6303508") or ("6271551") or ("6005284") or ("5969407") or ("5726477") or ("5648288") or ("5376560") or ("5372952") or ("5064773") or ("4933295") or ("5459089") or ("5399883") or ("5318915") or ("20010025987") or ("6319798") or ("6333244") or ("6255154") or ("6207518") or ("6146934") or ("6072216") or ("6054386") or ("6008099") or ("5986311") or ("5970353") or ("5874768") or ("5825066") or ("5795808") or ("5338945") or ("5322802") or ("5270227") or ("4835112") or ("6323518") or ("6268640") or ("6225151") or ("5258633") or ("5086332") or ("6429077") or ("6426258")).PN.	USPAT; US-PGPUB	2002/10/20 15:41			0
32	BRS	L32	27	23 and 31	USPAT; US-PGPUB	2002/10/20 15:44			0
33	BRS	L33	27	32 and 28	USPAT; US-PGPUB	2002/10/20 15:45			0